4. The method of claim 3 wherein a portion of the first barrier layer formed on the bottom of the hole is removed using etching techniques.

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5. The method of claim 4 wherein the metal layer deposited in the hole is copper.

6. The method of claim 5 wherein the metal layer is deposited using chemical vapor deposition techniques.

7. The method of claim 5 wherein the metal layer is deposited using physical vapor deposition techniques.

8. The method of claim 1 wherein the first barrier layer comprises Si_xN_y.

9. The method of claim 8 wherein the second barrier layer comprises a material selected from the group consisting of Ta, TaN, TaSiN, TiSiN and combinations thereof.

10. The method of claim 9 wherein the metal layer sputter deposited in the hole is copper.

11. The method of claim 10 wherein the second barrier layer is sputter deposited under the conditions of a high density plasma.

12. The method of claim 11 wherein the metal is sputter deposited under the conditions of a high density plasma.

13. The method of claim 12 wherein the metal is heated to a temperature of between about room temperature and about 500°C and then subjected to a pressurized environment.

14. The method of claim 13 wherein the pressurized environment is in the range of about 1000 psi to about 100,000 psi.

15. A method of filling a hole through a dielectric layer in an integrated circuit, comprising:

a) depositing a first barrier layer over a blanket dielectric layer;

b) forming a hole through the barrier layer and the dielectric layer to expose an underlayer;

c) depositing a second generally conformal barrier layer in the hole;

d) removing the barrier layer formed at the bottom of the hole;

e) selectively depositing a metal layer in the hole.

16. The method of claim 15 wherein the first barrier and second barrier layers are comprised of Si_xN_y.

17. The method of claim 16 wherein the first and second barrier layers are formed using chemical vapor deposition techniques.

18. The method of claim 17 wherein the barrier layer formed on the bottom of the hole is removed by sputter etching techniques.

19. (Restricted) An integrated processing tool, comprising:

a central transfer chamber having a robot assembly disposed at least partially therein for moving substrates;

a chemical vapor deposition chamber for depositing Si_xN_y;

a high density plasma physical vapor deposition chamber connected to the transfer chamber having a target comprising tantalum;

an etch chamber capable of achieving a high density plasma; and

a high density plasma physical vapor deposition chamber connected to the transfer chamber having a target comprising copper.

20. The method of claim 5 wherein the metal layer is deposited by first depositing a wetting layer using chemical vapor deposition techniques and then filling the hole using physical vapor deposition techniques.